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2SK2593G

Silicon N-channel junction FET

For low-frequency amplification

For switching circuits

■ Features

- Low noise figure NF
- High gate-drain voltage (source open) V_{GDO}
- SSMini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Package

- Code
SSMini3-F3
- Pin Name
1: Source
2: Drain
3: Gate

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	55	V
Gate-drain voltage (Source open)	V_{GDO}	-55	V
Gate-source voltage (Drain open)	V_{GSO}	-55	V
Drain current	I_D	30	mA
Gate current	I_G	10	mA
Power dissipation	P_D	125	mW
Channel temperature	T_{ch}	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Marking Symbol: 2B

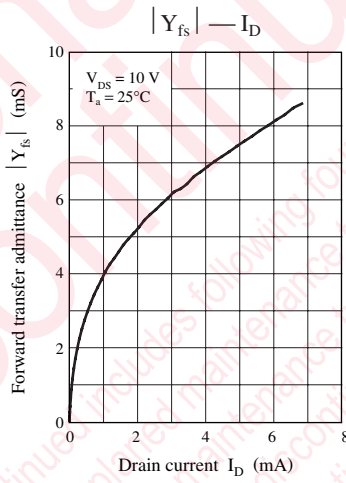
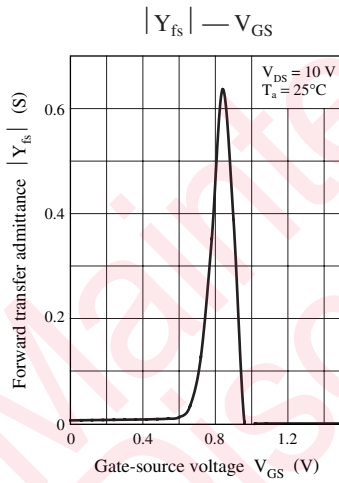
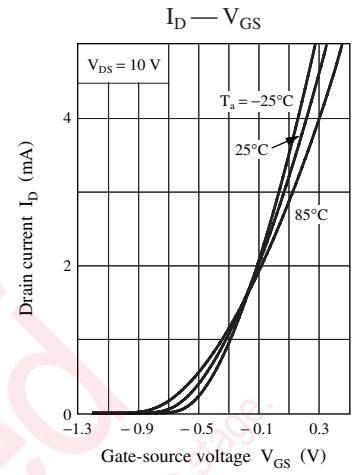
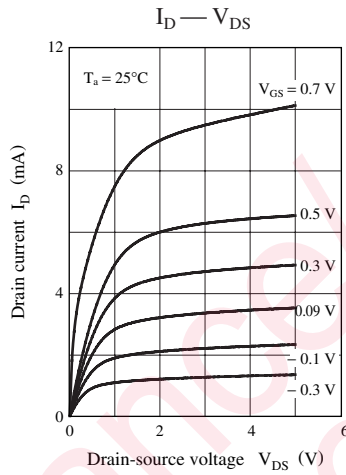
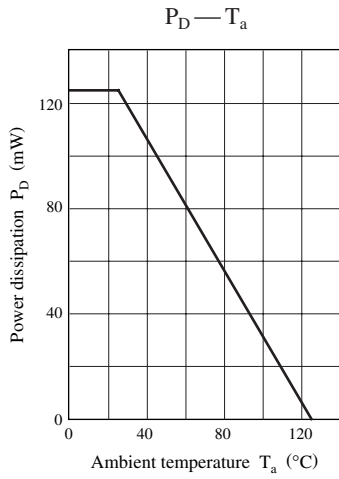
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Gate-drain surrender voltage	V_{GDS}	$I_G = -100 \mu\text{A}, V_{DS} = 0$	-55			V
Drain-source current *	I_{DSS}	$V_{DS} = 10 \text{ V}, V_{GS} = 0$	1.0		6.5	mA
Gate-source cutoff current	I_{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$			-10	nA
Gate-source cutoff voltage	V_{GSC}	$V_{DS} = 10 \text{ V}, I_D = 10 \mu\text{A}$			-5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ mA}, f = 1 \text{ kHz}$	2.5	7.5		mS
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		6.5		pF
Reverse transfer capacitance (Common source)	C_{rss}			1.9		pF
Noise figure	NF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 100 \text{ Hz}$ $R_g = 100 \text{ k}\Omega$		2.5		dB

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

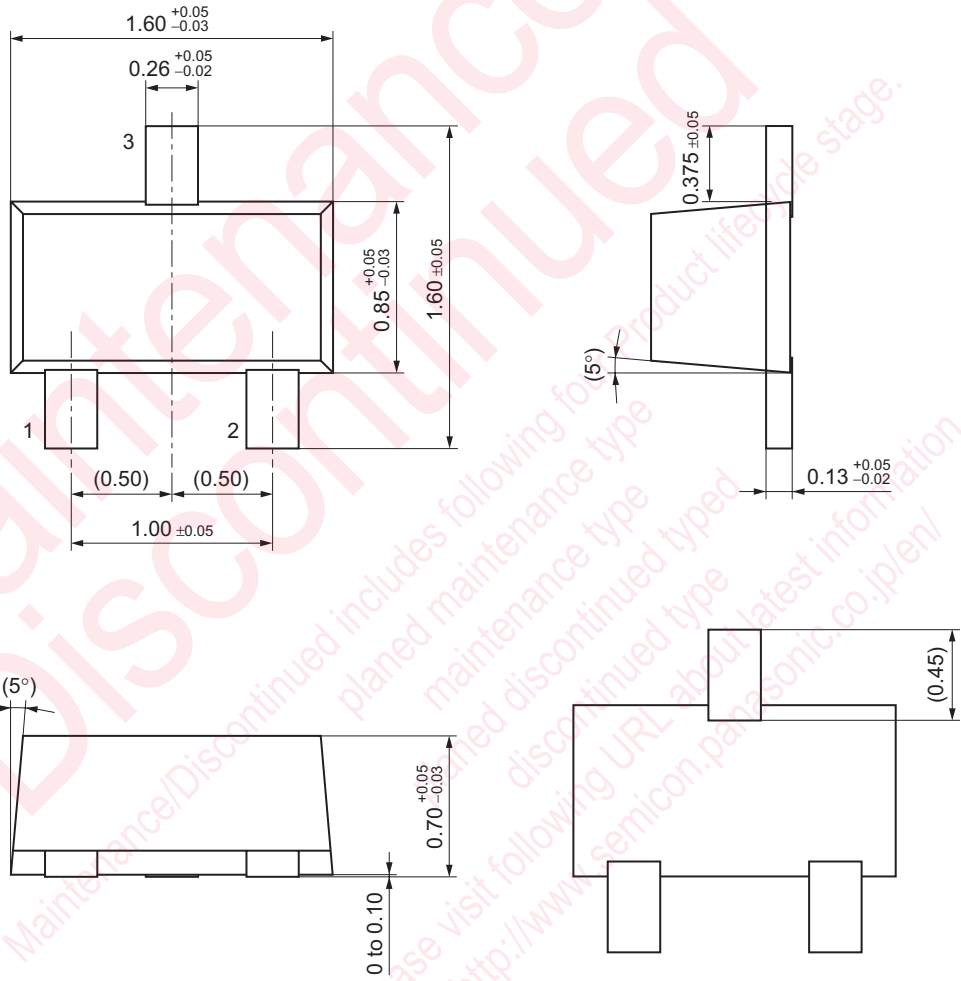
2. *: Rank classification

Rank	P	Q
I_{DSS} (mA)	1.0 to 3.0	2.0 to 6.5



SSMini3-F3

Unit: mm



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